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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/756,122	01/13/2004	Wai-Fan Yau	AMAT/2592.C7/DSM/LOW K/JW	4554
44257	7590	09/25/2007	EXAMINER	
PATTERSON & SHERIDAN, LLP 3040 POST OAK BOULEVARD, SUITE 1500 HOUSTON, TX 77056			MALDONADO, JULIO J	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary	Application No. 10/756,122	Applicant(s) YAU ET AL.	
	Examiner Julio J. Maldonado	Art Unit 2823	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 29 June 2007.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 11-13, 15-18 and 21-28 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 11-13, 15-18 and 21-28 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|---|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08)
Paper No(s)/Mail Date <u>07/11/2007</u> . | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 11-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chiang et al. (U.S. 5,817,572, hereinafter Chiang) in view of Sugahara et al. (U.S. 5,989,998, hereinafter Sugahara).

Chiang (Figs.15-25) teaches a method of forming interconnect structures including providing a substrate (320) having a contact (321) formed therein (Chiang, column 12, lines 52 – 63); depositing a first dielectric layer (322) on said substrate (320) (Chiang, column 13, lines 15 – 35); forming an etch stop layer (323) on said first dielectric layer (322) (Chiang, column 14, line 61 – column 15, line 4); forming a second dielectric layer (350) on said etch stop layer (323) (Chiang, column 15, lines 28 – 46); forming a photoresist layer (352) on said second dielectric layer (350) (Chiang, column 15, lines 48 – 58); and using said photoresist layer to form a contact hole (351) in said second dielectric layer (350) (Chiang, column 15, lines 59 – 62), wherein said first dielectric layer (322) and said second dielectric layer (350) may include any suitable dielectric material or materials including silicon dioxide, silicon nitride, silicon oxynitride, phosphosilicate glass, borophosphosilicate glass, fluoropolymer, parylene, polyimide, any suitable spin-on glass, or any suitable spin-on polymer (Chiang, column 13, lines 15

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– 35 and column 15, lines 28 – 46), and further forming a third dielectric layer (395) over said second dielectric layer (Chiang, column 21, lines 4 – 15).

Chiang fails to disclose using a low dielectric constant material. However, parylene, polyimide, for example, are known low dielectric constant materials.

Therefore, Chiang teaches upon the claimed invention.

Chiang fails to teach wherein the low dielectric constant material is a an oxidized organosilane layer, wherein said organosilane layer is deposited in a plasma enhanced process from a mixture comprising an organosilane compound and an oxidizing gas and wherein the carbon content of the low dielectric constant oxidized organosilane layer is form 1% to 50% by atomic weight.

However, Sugahara (Figs.3a-d) teaches a method of depositing on a substrate (200) a plurality of layers (202-204), wherein one or more of the layers (202, 204) is a low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising an organosilane compound an oxidizing gas, wherein said organosilane compound is selected from a phenylsilane group or a vinylsilane group; and etching said one or more of said layers in a patterning process, wherein the carbon content of said oxidized organosilane layer is, for example, 25.7% (first embodiment, chemical formula 2) or 22.2% (ninth embodiment, chemical formula 15) (Sugahara, column 7, line 66 – column 8, line 8, line 34, column 8, line 58 – column 11, line 53 and column 18, line 25 – column 21, line 53).

Sugahara fails to expressly teach wherein said oxidized organosilane layer has a carbon content from 1% to 50%. However, in the case where the claimed ranges "overlap or lie inside ranges disclosed by the prior art" a prima facie case of obviousness exists. MPEP 2144.05. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to use the dielectric layer with the carbon concentration disclosed in the teachings of Sugahara to arrive at the claimed invention.

It would also have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Chiang and Sugahara to enable forming a low dielectric layer in Chiang as taught by Sugahara for the further advantage of forming a film with improved film formability and cost efficiency (Sugahara, column 3, lines 25 – 30) and because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable methods of forming the disclosed dielectric layer in Chiang and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

3. Claims 15-18, 21 and 23-28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chiang ('572) in view of Shu et al. (Patent Application, 09/019,900, hereinafter Shu).

In reference to claims 15-18, 23, 24, 26-28, Chiang (Figs.15-25) teaches a method of forming interconnect structures including providing a substrate (320) having a contact (321) formed therein (Chiang, column 12, lines 52 – 63); depositing a first dielectric layer (322) on said substrate (320) (Chiang, column 13, lines 15 – 35); forming

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an etch stop layer (323) on said first dielectric layer (322) (Chiang, column 14, line 61 – column 15, line 4); forming a second dielectric layer (350) on said etch stop layer (323) (Chiang, column 15, lines 28 – 46); forming a photoresist layer (352) on said second dielectric layer (350) (Chiang, column 15, lines 48 – 58); and using said photoresist layer to form a contact hole (351) in said second dielectric layer (350) (Chiang, column 15, lines 59 – 62), wherein said first dielectric layer (322) and said second dielectric layer (350) may include any suitable dielectric material or materials including silicon dioxide, silicon nitride, silicon oxynitride, phosphosilicate glass, borophosphosilicate glass, fluoropolymer, parylene, polyimide, any suitable spin-on glass, or any suitable spin-on polymer (Chiang, column 13, lines 15 – 35 and column 15, lines 28 – 46), and further forming a third dielectric layer (395) over said second dielectric layer (Chiang, column 21, lines 4 – 15).

Chiang fails to disclose forming the second dielectric layer using a low dielectric constant material. However, parylene, polyimide, for example, are known low dielectric constant materials. Therefore, Chiang teach upon the claimed invention.

Chiang fails to teach wherein the low dielectric constant organosilane layer is deposited in a plasma enhanced process from a mixture comprising a methylsilane compound and an oxidizing gas, the carbon content of the low dielectric constant oxidized organosilane layer is form 1% to 50% by atomic weight.

However, Shu in a related method to form interconnect structures teaches forming a low-k dielectric layer over a substrate, wherein said dielectric layer is deposited in a plasma enhanced process from a mixture comprising a reactant species

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or a combination of reactant species which includes carbon and silicon, such as 3-methyltrimethoxysilane, labeled methylsilane compound, and an oxidizing gas such as O_2 and H_2O_2 (page 4, lines 9 – 22). It would have been within the scope of one of ordinary skill in the art to combine the teachings of Chiang and Shu to enable forming the low-k dielectric layers of Chiang according to the teachings of Shu because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable methods of forming the second dielectric layer of Chiang et al. and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

The combination of Chiang et al. and Shu fail to disclose wherein the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight. However, the same material would be treated in the same manner and therefore the recited results would be obtained.

In reference to claims 21 and 25, the combined teachings of Chiang and Shu fail to disclose wherein the methylsilane compound is methyl silane (CH_3SiH_3). However, Shu teach wherein said dielectric layer is deposited in a plasma enhanced process from a mixture comprising a reactant species or a combination of reactant species which includes carbon and silicon, and an oxidizing gas such as O_2 and H_2O_2 (Shu, page 4, lines 9 – 22). The combination of Chiang and Shu further teach that conventional materials in the art to form oxide layers include methyl silane (CH_3SiH_3) (Shu, page 3, line 25 – page 4, line 1). Therefore, since methyl silane (CH_3SiH_3) is a conventional material used in the fabrication of oxide layers and the prior art of record is open to form

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a dielectric layer from a mixture comprising a reactant species or a combination of reactant species which includes carbon and silicon, one of ordinary skill in the art at the time the invention was made would have been envisioned to use said methyl silane to form said dielectric layer.

4. Claim 22 is rejected under 35 U.S.C. 103(a) as being unpatentable over Chiang ('572) in view of Shu ('900) as applied to claims 15-18, 21 and 23-28 above, and further in view of Chen (U.S. 5,970,376).

The combination of Chiang and Shu substantially teach the claimed invention but fail to disclose etching the low dielectric constant oxidized organosilane layer using fluorine, carbon, and oxygen ions. However, Chen (Figs.4-7) in a related method to form interconnect structures teaches the steps of forming a low dielectric layer (32) over a substrate (30), wherein said dielectric layer has the general formula $R_1\text{-Si(OR}_2\text{)}_3$, wherein R_1 is hydrogen and R_2 is CH_3 ; and etching the low dielectric layer (32) using fluorine, carbon, and oxygen ions (Chen, column 4, line 66 – column 5, line 12, column 5, lines 34 – 56, column 7, lines 25 – 42, and column 8, lines 40 – 48). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Chiang and Shu with Chen to enable etching the dielectric layer of Chiang and Shu according to the teachings of Chen for the further advantage of forming vias with attenuated lateral etching of said vias (Chen, column 4, lines 39 – 63).

Response to Arguments

5. Applicant's arguments filed 06/29/2007 have been fully considered but they are not persuasive.

Applicants argue, "...Applicants submit that as *Chiang, et al.* does not provide any guidance regarding what constitutes a "suitable" dielectric material other than listing specific dielectric materials, *Chiang, et al.* does not suggest or motivate using a low dielectric constant oxidized organosilane layer as the dielectric material. Applicants further submit that the Examiner's observation that *Chiang, et al.* is open to different materials as the dielectric films is not sufficient to find a teaching or suggestion to use the oxidized organosilane layer of *Sugahara, et al.* as the dielectric layer of *Chiang, et al.* Thus, Applicants respectfully submit that the combination of *Chiang, et al.* and *Sugahara, et al.* does not suggest or motivate using *Sugahara, et al.*'s oxidized organosilane layer as the dielectric layer in *Chiang, et al.*'s stack of layers...".

In response to this argument, as stated in the office action mailed 04/24/2007, in response to this argument, *Chiang* teaches forming interlevel dielectric layers to be used to form interconnect structures, wherein said layers are made of any suitable material including silicon dioxide, silicon nitride, silicon oxynitride, phosphosilicate glass, borophosphosilicate glass, fluoropolymer, parylene, polyimide, any suitable spin-on glass, or any suitable spin-on polymer (*Chiang*, column 13, lines 21 – 35 and column 15, lines 28 – 46). Furthermore, The transitional term "comprising", which is synonymous with "including," "containing," or "characterized by," is inclusive or open-ended and does not exclude additional, unrecited elements or method steps. See

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MPEP 2111.03. Therefore, Chiang is open to different unrecited materials used to form interlayer dielectric films in the formation of interconnect structures, such as the low dielectric constant oxidized organosilane layer comprising carbon disclosed in Sugahara (Sugahara, column 7, line 66 – column 8, line 8, line 34, column 8, line 58 – column 11, line 53 and column 18, line 25 – column 21, line 53). Furthermore, both Chiang and Sugahara are directed to the same field of endeavor, that is, the formation of interconnect structures and one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable methods of forming the disclosed dielectric layer in Chiang and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

Applicants also argue, "...*Shu, et al.* describes oxidizing a reactant comprising carbon to deposit a SiOC low dielectric constant film but does not teach or suggest including the low dielectric constant film in a plurality of layers that also comprises a top layer that is a photoresist...". In response to this argument, Shu was not relied upon that limitation. Furthermore, Chiang and Shu are directed to the formation of multilevel interconnect structures, and one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable methods of forming the disclosed dielectric layer in Chiang and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

Conclusion

6. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Shu et al. (U.S. 6,348,421 B1) teaches a method of depositing dielectric layers using methylsilane as a source gas (Shu et al., column 3, lines 39 – 44).

8. Applicants are encouraged, where appropriate, to check Patent Application Information Retrieval (PAIR) (<http://portal.uspto.gov/external/portal/pair>) which provides applicants direct secure access to their own patent application status information, as well as to general patent information publicly available.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Julio J. Maldonado whose telephone number is (571) 272-1864. The examiner can normally be reached on Monday through Friday.

10. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith, can be reached on (571) 272-1907. The fax number for this

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group is 571-273-8300. Updates can be found at

<http://www.uspto.gov/web/info/2800.htm>.



Julio J. Maldonado
April 5, 2007

Julio J. Maldonado
Patent Examiner
Art Unit 2823



MATTHEW SMITH
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800